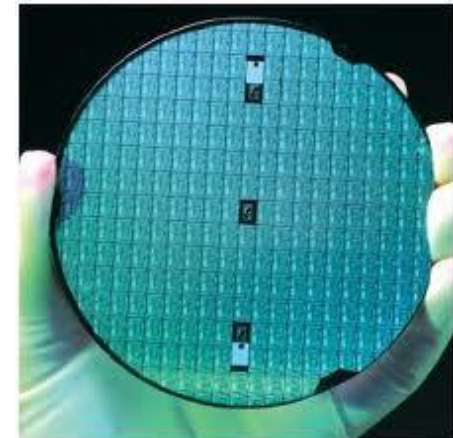
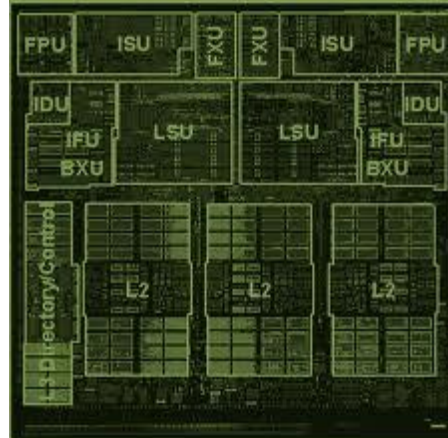
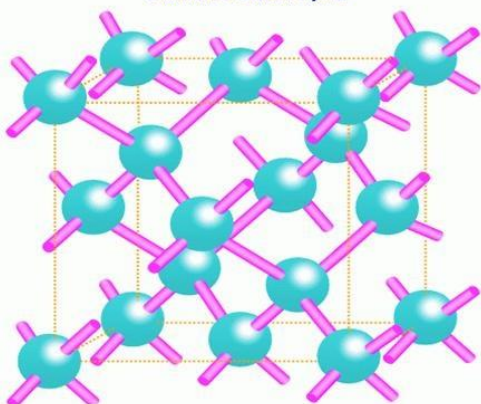


Structure of silicon crystal



ECE 122A

VLSI Principles

Lecture 1

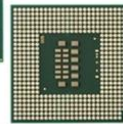
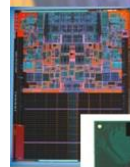
Prof. Kaustav Banerjee
Electrical and Computer Engineering
University of California, Santa Barbara
E-mail: kaustav@ece.ucsb.edu

Why VLSI?

❑ Difficult to imagine life without **integrated circuits**....

❑ Applications in:

- Consumer Electronics
- Computing
- Communication
- Medical/Health
- Entertainment
- Energy
- Aerospace
- Automobile
- Military



Electronics inside a BMW...

http://www.bmw.com/com/en/insights/technology/technology_guide/articles/digital_motor_electronics.html

Digital Motor Electronics (DME).

The comprehensive management system for your engine: Digital Motor Electronics (DME) **controls all key aspects of the engine's operation**, ensuring optimum reliability, maximum performance and the lowest possible fuel consumption and emissions.

By managing key engine functions, Digital Motor Electronics (DME) **guarantees optimum reliability, maximum performance and the lowest possible fuel consumption and emissions**. Its sensors continually all factors affecting the operation of the engine. The data is then evaluated by a microprocessor and translated into commands for the fuel injection and ignition systems.

The DME system **receives up to 1,000 separate items of data input per second**, including engine speed, air intake volume, air temperature and density, coolant temperature, throttle position, accelerator position and vehicle speed.

DME verifies all incoming data by comparing it with the reaction of the rest of the system. If a defective sensor delivers unrealistic data, DME replaces this with preset standard values. If a spark plug fails, DME immediately cuts fuel flow to this cylinder in order to prevent engine damage.

DME **looks after the electrical power system too, with sensors measuring the charge and condition of the battery as well as current electrical power consumption**. By maintaining optimum battery charge levels and thus avoiding flat batteries, it prevents damage to the battery and guarantees maximum battery life, thereby helping to ensure the engine always starts readily.

BMW introduced the world's first Digital Motor Electronics system in the BMW 732i in 1979.



BMW Z4 Roadster



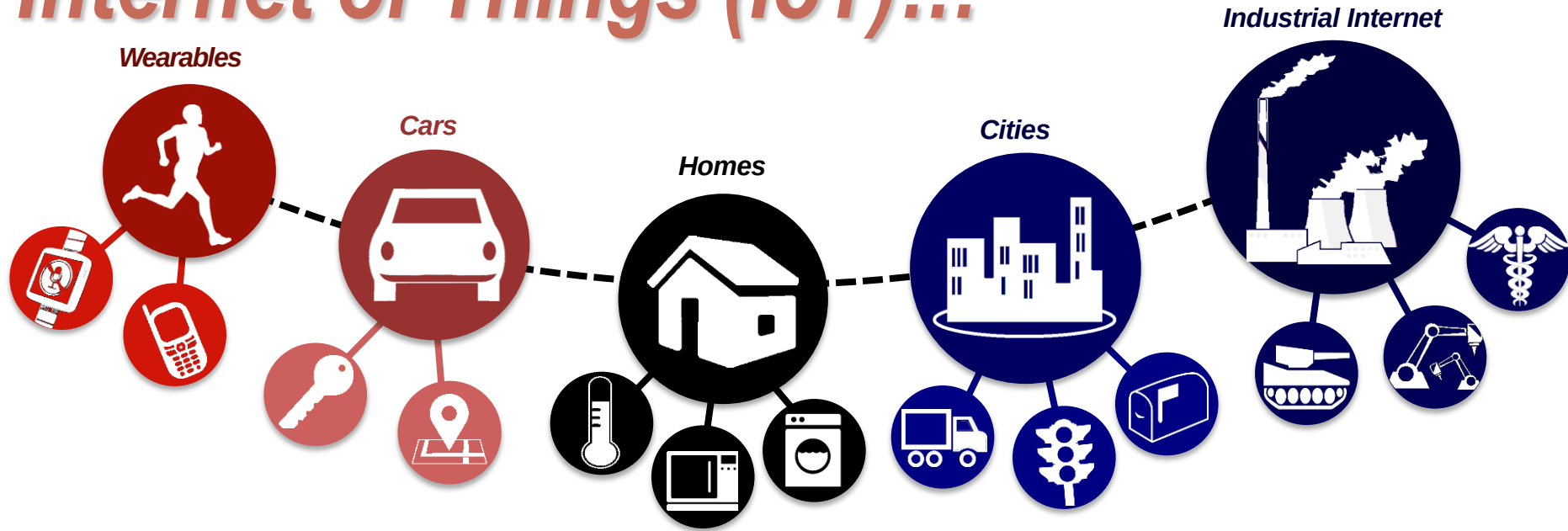
VLSI inside...

Hard drive of a PC



Digital Mobile Phones

Internet of Things (IoT)...



- 1990s' fixed Internet wave connected 1 billion users
- 2000s' mobile wave connected another 2 billion
- The IoT has the potential to connect 28 billion “things” by 2020
— **The third wave of Internet development**

Bottom Line:

To enable IoT - need low power sensors and ICs....

What is VLSI?

- ❑ Very Large Scale Integrated ~~Circuits~~ Systems
- ❑ **Very-large-scale integration (VLSI)** is the process of creating *integrated systems* by combining *billions* of transistors into a single chip.

1971: Intel 4004

**2300 Transistors...with CPU, memory
and input/output controls**



2008: Intel® Xeon® Processor MP X7460--**1.9 Billion Transistors!!!**

For details on Intel Microprocessors:

<http://www.intel.com/pressroom/kits/quickreffam.htm>

Amazing Transistor Scaling....

- *If transistors were people*



2300
Average Music Hall
capacity



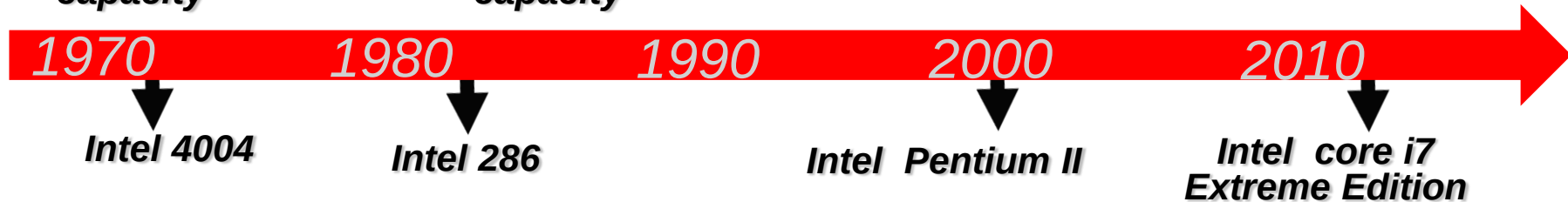
134000
Large stadium
capacity



32 Million
Population of Tokyo



1.3 Billion
Population of China



Now imagine 1.3 Billion people in the original music hall!!!!

Why Scaling?

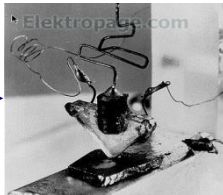
- Higher number of devices in chip
- Faster operation
- More functionality and lower cost

Scaling Challenges

- Higher power consumption
- Severe short-channel effects
- Higher leakage

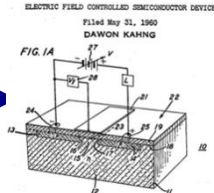
History...

First point contact Transistor,
Shockley, Brattain, Bardeen
Bell Labs



1959

First FET, Kahng
Bell Labs



1964

First Microprocessor,
Intel

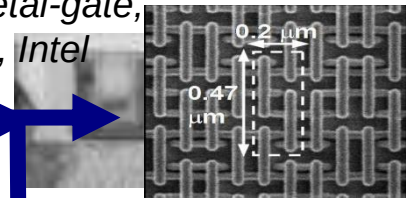


1998

First FinFET,
C. Hu, Berkeley



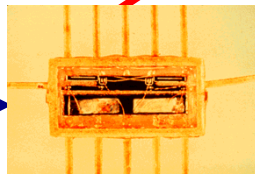
High-k Metal-gate,
32nm, Intel



2011

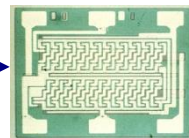
FinFET SRAM

1948



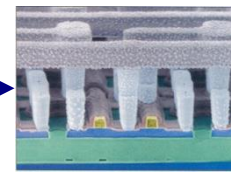
First IC,
Jack Kilby, TI
Robert Noyce,
Fairchild

1960



First MOS IC,
Robert Norman

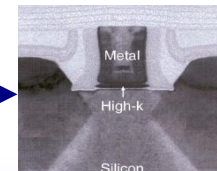
1970



First SOI IC,
IBM

1999

2009



High-k Metal-gate,
45 nm, Intel

8

2011: a paradigm shift

Introducing the world's first 3-D transistors ready for high volume manufacturing



For
IT Ce

ARCHITECTURE AND SILICON

Microarchitecture
Silicon Technology

PRODUCTS TECHNOLOGIES

MANUFACTURING

RESEARCH

STANDARDS

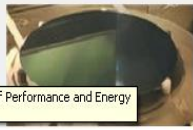
SECURITY



Unprecedented Combination of Performance and Energy Efficiency

Unprecedented Combination of Performance and Energy Efficiency

22nm EXPLAINED



Watch Mark T. Bohr Intel Senior Fellow explain 22nm >

Home > Technology > Architecture & Silicon > Silicon > Intel 22nm Technology

INTRODUCING THE WORLD'S FIRST 3-D TRANSISTOR READY FOR HIGH-VOLUME MANUFACTURING

3-D, 22nm: New Technology Delivers An Unprecedented Combination of Performance and Power Efficiency

Intel is introducing a different technology for future microprocessor families: 3-D transistors manufactured at 22nm. These new transistors enable Intel to continue to relentlessly pursue Moore's Law and to ensure that the pace of

QUICK LINKS

- 32nm
- Silicon Technology
- Intel Microarchitecture code-name Sandy Bridge

ElectronicsWeekly.com

Other Companies may join Intel with 22 nm FinFET, says IMEC chief.

HOME NEWS DESIGN

You are in: Production | Manufacturing

Salary Survey 2011

ElectronicsWeekly.com



Take part in our Salary Survey and help nature nurture salary levels

Other companies may join Intel with 22nm Finfets, says Imec chief.

David Manners
Monday 23 May 2011 19:26

Other companies besides Intel may adopt Finfet at the 22nm generation of process technology, according to Luc van den Hove, President of Imec, Europe's foremost microelectronics research establishment.

"Some companies may adopt Finfet at the second generation of 22nm," van den Hove told EW in Brussels today.

Share the content

ShareThis

Most Viewed

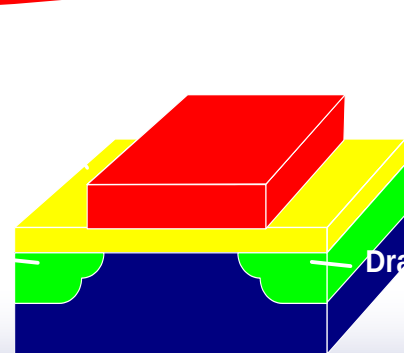
Related Jobs

Senior Verification Engineer/ Lead - Semiconductors - Germany - JB5383 Europe/Germany Eng

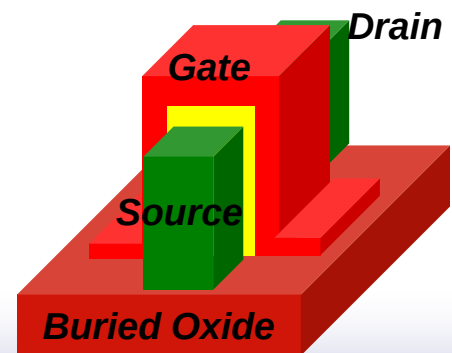
Resources

Li-Fi flickers to challenge Wi-Fi
Posted: 10:11 29 Jul 2011

TSMC to ramp 14nm finfets in

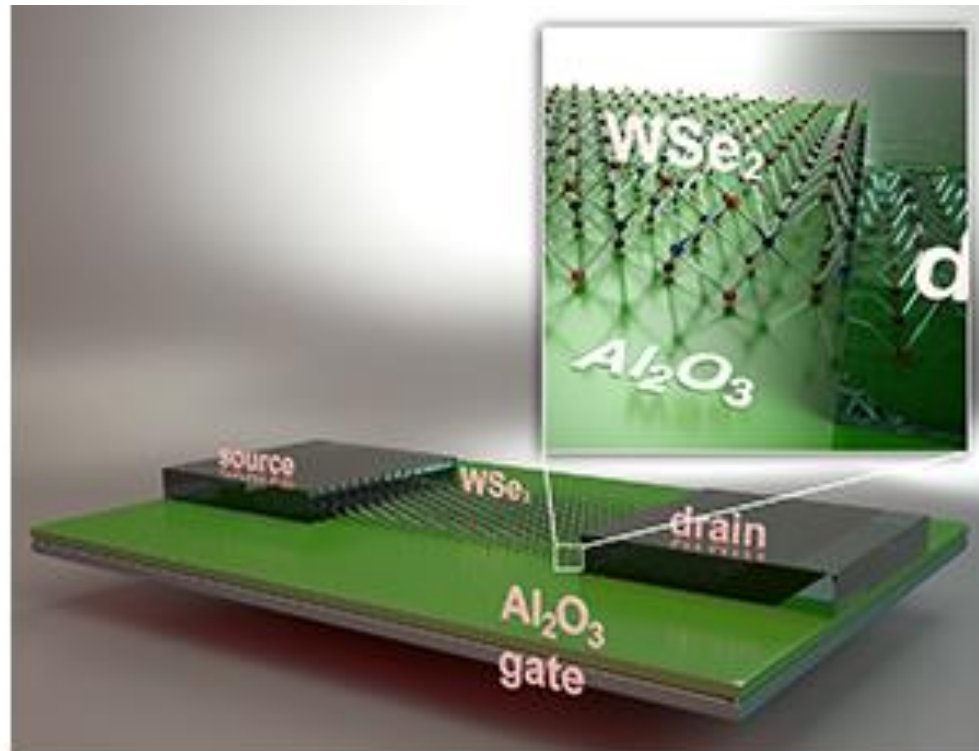


Planar MOSFET



FinFET

Ultimate Thin-body Transistors



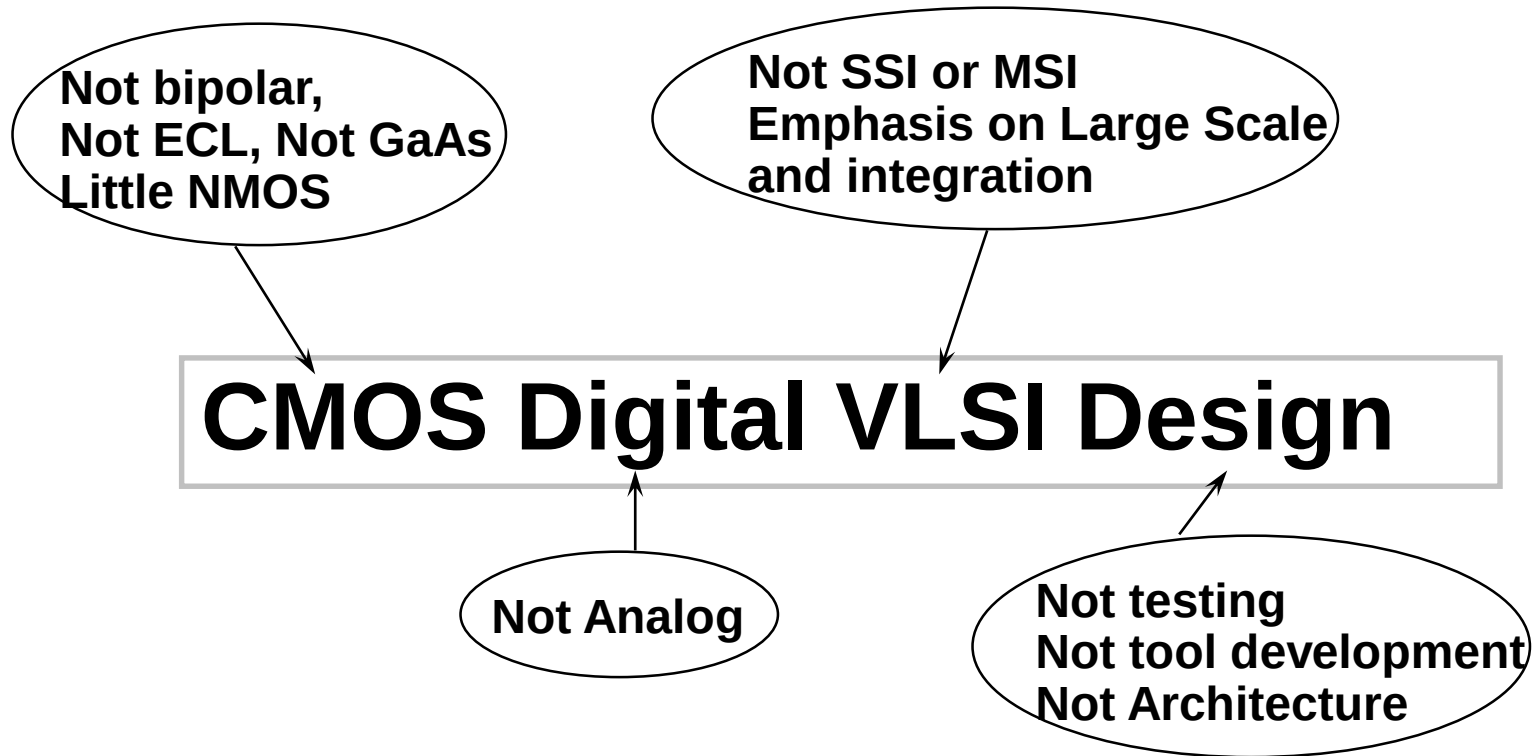
Schematic view of a back-gated field effect transistor fabricated by UCSB researchers using monolayer tungsten diselenide (WSe₂) channel material. Credit: Peter Allen, UCSB

Read more: <http://engineering.ucsb.edu/news/711>

Who should be taking this course?

- Those interested in pursuing career in *nanoelectronics, bioelectronics etc*: transistor design, circuit design, or computer-aided design
 - Those interested in exploring “*emerging devices and technology*” driven circuit/system design
 - Those interested in passing the *ECE PhD Screening Exam* in the VLSI & CMOS Design Area
 - Those interested in finding a *lucrative position in the semiconductor industry* as an IC design engineer
- ❖ *In the past, students recruited by Intel, AMD, IBM, TI, SanDisk, nVidia, Marvel, Global Foundries, Maxim, Micron Technology and other IC companies have found the course invaluable...*

About this course.....



What to expect out of the course...

❑ **The course is:**

- To learn **transistor level design** of logic gates, components
- to learn **practical aspects** of design including design trade-offs

❑ **The course is not:**

- A tutorial to build expertise in CAD tools, or
- A forum to demonstrate architecture skills, or
- A test of your logic design expertise, or
- An exercise to design a microprocessor.

❑ **Course time is short: < 20 classes**

- A lot of self-study is expected
- Homeworks and assignments could be time consuming—but a key component of this course
- Project is a major commitment and calls for a lot of hard work!

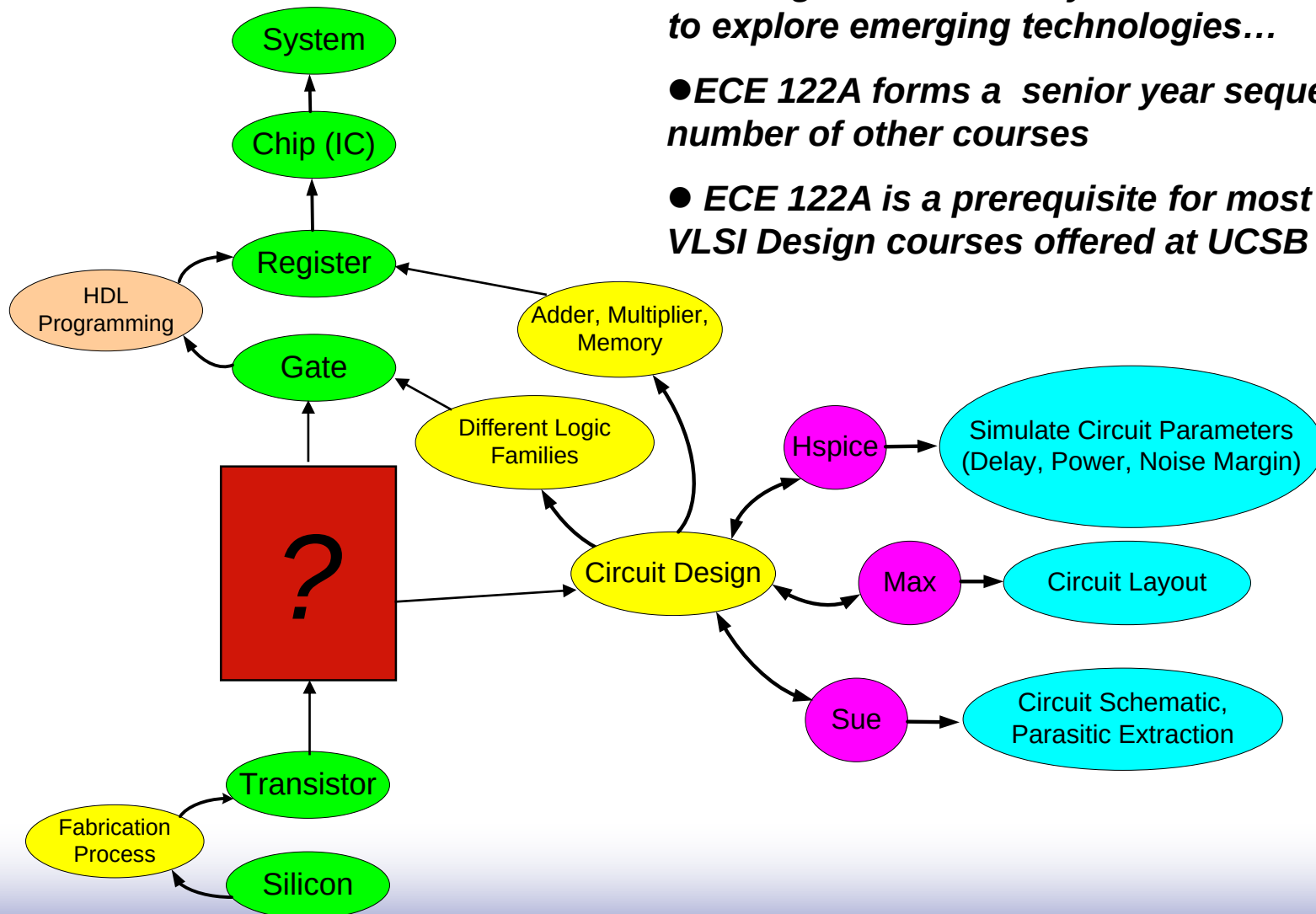
❑ **This is not a class just to improve your GPA!**

Why take this course?

- *This is what you will need to do anything meaningful in circuits/systems research as well as to explore emerging technologies...*

- *ECE 122A forms a senior year sequence with a number of other courses*

- *ECE 122A is a prerequisite for most advanced VLSI Design courses offered at UCSB*



What are we going to cover?

- ❑ **Introduction to digital integrated circuits.**
 - **CMOS devices** and manufacturing technology. CMOS inverters, **gates** and **interconnects**. **Circuit characterization**: delay, noise margins, and power dissipation. **Combinational** and **sequential** circuits. **Arithmetic operations** and **memories**
- ❑ **What will you learn?**
 - **Understanding, designing, and optimizing digital circuits** with respect to different quality metrics: area, speed, power dissipation, and reliability using analytical methods and circuit simulation
 - **Practical aspects of IC design**: impact of manufacturing variations (device level variations) on circuit level metrics, effect of device and interconnect parasitics on circuit performance
 - **Learn to use various IC design tools**: Layout, Extraction, Circuit simulation

Textbook and References

❑ Textbook

- *CMOS VLSI Design: A Circuits and Systems Perspective*
(Fourth Edition, 2011)
 - by Neil H. E. Weste and David Harris
 - Addison Wesley Publishing Company

❑ Supplementary Text:

- *Modern Semiconductor Devices for ICs*
(First Edition, 2010)
 - by Chenming Hu
 - Prentice Hall Publishing Company

❑ Lecture Notes: Combination of slides + discussion

- Only slides will be posted on the class web page

❑ Reference Materials and Recommended Reading

- Will be posted on the class web site:

Class Home Page:

http://www.ece.ucsb.edu/courses/ECE122/122_F15Banerjee/

Prerequisites

- ❑ Logic Design (ECE 152A or equivalent) ...at least ECE 15A
 - Combinational and clocked logic, gates, latches, flip-flops, etc.
 - Logic reduction: K-maps
- ❑ Fundamentals of EE
 - ❑ Resistance, capacitance, inductance, power/energy
- ❑ Circuit Analysis (both analytical and simulation based)
 - ❑ at the level of ECE 2A, 2B and 2C
- ❑ Semiconductor and Device Physics (basics will be covered in this course)
 - ❑ Energy band diagrams, p/n junctions, MOS transistors

....Most important prerequisite is your desire to excel!!

Homework, Exams, Grading (1)

- ❑ **Homeworks:** will be posted on the class home page
 - Weekly HW/Lab assignments
 - Late homework will be penalized (20% per day), submission (beyond the second day) will get ZERO grade
 - Solutions will be Posted on the class web site a week after the due date
 - Homework assignments require Lab work
 - All Labs MUST be completed for passing
 - **Will count towards 20% of the final grades**
- ❑ **Exams**
 - Midterm Exam: **Will count towards 20% of the final grades**
 - FINAL Exam: **Will count towards 40% of the final grades**
- ❑ **Final Project:** must complete to pass
 - Will be posted on class home page
 - **Will count towards 20% of the final grades**
- ❑ **No “make-up” homework, exams, labs**

Homework, Exams, Grading (2)

❑ Project

- You may work as part of a team (not more than 2), yet graded individually
 - Your grade = Oral questioning by TAs + project report
- The project report MUST summarize the contribution of both students

❑ Final grades

- Distribution of grades depends on class performance
- Standard grading techniques will be applied (histograms, curves)--- same criteria for all students
 - ❑ *No incomplete grade (no exceptions)*

Class Calendar

Lectures		Homework	Covered Topics	Lab & Project	
9/ 29	Lecture 1	Homework 1 (10/01) Digital Design Review Due 10/09	Boolean Algebra	Lab 1 Environment	
10/ 1	Lecture 2		Combinational Circuit	Setup and Practice	
10/ 6	Video I & II		Sequential Circuit	10/06	
10/ 8	Lecture 3	Homework 2 (10/08) CMOS and Pass Transistors Due 10/16	Moore’s Law	Due 10/16	
10/13	Lecture 4		CMOS Implement	Lab 2 HSpice, CMOS	
10/15	Lecture 5		Pass Transistor	Sizing	
			Transmission Gate	10/13	
			Multiplexer	Due 10/23	
			Finite-State-Machine		
			Euler Path		
10/20	Lecture 6	Homework 3 (10/15) Semiconductor Physics Due 10/23	Carrier Statistics	Lab 3 Static CMOS	
10/22	Lecture 7		Current in Semiconductor	10/20	
			PN Junction	Due 10/30	
			MOS Capacitor		
10/27	Lecture 8	Homework 4 (10/22) MOSFET and CMOS Inverter Due 10/30	Threshold Voltage	Lab 4 Inverter	
10/ 29	Lecture 9		Body Bias	10/27	
			Current Saturation	Due 11/06	
			Device Parasitics		
			CMOS Inverter		
11/ 3	Lecture 10	Homework 5 (10/29) Inverter, CMOS Sizing, Interconnect Due 11/13		Final Project Starts from 11/01	
11/ 5	Midterm				
11/10	Lecture 11				
11/12	Lecture 12				
11/17	Lecture 13	Homework 6 (11/12) Logic Design Styles Due 11/23	Ratioed Logic		
11/19	Lecture 14		Pass Transistor Logic		
11/24	Lecture 15		Dynamic Logic		
11/26	Holiday				
12/ 1	Lecture 16	Homework 7 (11/23) Sequential Logic and Memory Due 12/ 4			
12/ 3	Review		Sequential Logic		
			DRAM		
			SRAM		
Final Exam: 12/10 (Thursday) 4:00 – 7:00 PM					
Project Report Due: 12/12 (Saturday)					

Preparation for the course

- ❑ Computing environment and tools
 - Setup computer account, and the compute environment
 - Familiarize with the schematic and layout editors (**SUE, MAX**)
 - Familiarize with extractor (**CALIBER-Mentor Graphics**)
 - Familiarize with the circuit simulator (**HSPICE**)
 - **Tutorials** on these tools are posted on the class web page
- ❑ Theory
 - Review logic design (ECE 152A)
 - Review device physics (I will provide some tutorial material to help you)
- ❑ Project
 - You may start formalizing your project team

A few hints

❑ Homeworks

- **Most important** part of the course....
- Spend most of the time thinking, planning, and exploring on your own
- Discussions are encouraged but **refrain from extracting the answers** from the TAs or other students
- Show your work on the homework! **Thought process is more important than final answer** → partial credit given
- Use simulators for verification of your design

❑ Difficult to take notes?

- Note down important points, not essays...all slides will be posted
- Read topics from the textbook BEFORE and AFTER the class

❑ Actively participate in the class discussion

- Don't be afraid if you are wrong

❑ Question everything, even the book